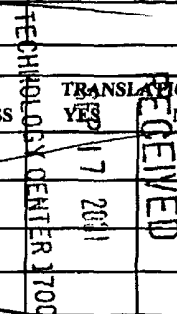
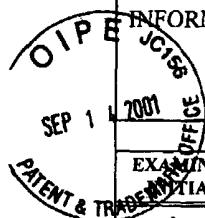


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INFORMATION DISCLOSURE STATEMENT (use several sheets if necessary)		APPLICANT Peter C. Van Buskirk, et al.		GROUP 1762 1263	
		FILING DATE June 5, 2001			
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EXAMINER INITIAL	PATENT NUMBER	ISSUE DATE	NAME	CLASS	FILING DATE IF APPROPRIATE
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OTHER DOCUMENTS (Including Author, Title, Journal-Date, Page Number, Etc.)					
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Continue on Page 2					
EXAMINER <i>Ala w Oba</i>			DATE CONSIDERED 12/1/03		
EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to the applicant.					



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